





TEXAS INSTRUMENTS

TRSF3222E SLLS823A – JULY 2007 – REVISED AUGUST 2021

# 3-V to 5.5-V Multichannel RS-232 Line Driver and Receiver with ±15-kV ESD Protection

## 1 Features

- ESD Protection for RS-232 bus pins
  - ±15-kV Human-body model (HBM)
  - ±8-kV IEC 61000-4-2, Contact discharge
  - ±15-kV IEC 61000-4-2, Air-gap discharge
- Meets or exceeds the requirements of TIA/ EIA-232-F and ITU v.28 standards
- Operates with 3-V to 5.5-V V<sub>CC</sub> supply
- Operates up to 1000 kbit/s
- Two drivers and two receivers
- Low standby current . . . 1 µA Typ
- External capacitors . . . 4 × 0.1 µF
- Accepts 5-V logic input with 3.3-V supply

## 2 Applications

- Industrial PCs
- Wired networking
- · Data center and networking equipment
- Notebooks
- Hand-held equipment

## **3 Description**

The TRSF3222E consists of two line drivers, two line receivers, and a dual charge-pump circuit with  $\pm$ 15-kV ESD protection pin to pin (serial-port connection pins, including GND).

The TRSF3222E meets the requirements of TIA/ EIA-232-F and provides the electrical interface

between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The TRSF3222E operates at typical data signaling rates up to

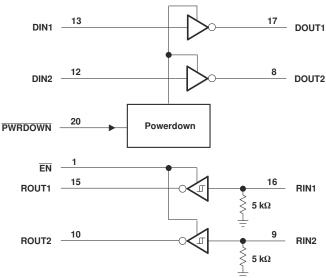
1000 kbit/s and is an improved drop-in replacement for industry-popular '3222 two-driver, two-receiver functions.

The TRSF3222E can be placed in the power-down mode by setting the power-down ( $\overline{PWRDOWN}$ ) input low, which draws only 1  $\mu$ A from the power supply. When the device is powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V<sub>CC</sub>, and V– is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable ( $\overline{EN}$ ) high.

	Device informatio	n
PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
	DB (SSOP) (20)	10.2 mm x 5.30 mm
TRSF3222E	DW (SOIC) (20)	15.4 mm x 7.50 mm
	PW (TSSOP) (20)	7.80 mm v 4.40 mm

**Device Information** 

 For all available packages, see the orderable addendum at the end of the data sheet.



A. Pin numbers shown are for the DB, DW, and PW packages.

## Logic Diagram (Positive Logic)

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision * (July 2007) to Revision A (August 2021)	Page
•	Updated the list of Applications	1
•	Deleted the Ordering Information table	1
•	Added the Device Information table, the Pin Configuration and Functions, the Detailed Description sectio	n,
	the Application and Implementation section	1
•	Deleted the Package thermal impedance from the Absolute Maximum Ratings	4
•	Added the ESD Ratings table	4
•	Added the ESD Ratings - IEC Specifications table	4
•	Added the Thermal Information table	<mark>5</mark>
•	Changed the value of $R_{\theta JA}$ for PW package (previously in the <i>Absolute Maximum Ratings</i> table), and additional thermal parameters for all packages in the <i>Thermal Information</i> table	



# **5** Pin Configuration and Functions

DB, DW,	OR PW	/ PA	CKAGE
	(TOP VI	EW)	)
1			1
EN [	1	20	PWRDOWN
C1+[	2	19	] V <sub>CC</sub>
V+[	3	18	] GND
C1-[	4	17	DOUT1
C2+[	5	16	RIN1
C2-[	6	15	ROUT1
V-[	7	14	] NC
DOUT2	8	13	DIN1
RIN2	9	12	DIN2
ROUT2	10	11	] NC
			1

NC - No internal connection

### Table 5-1. Pin Functions

PIN		I/O	DESCRIPTION		
NAME	NO.				
C1+	2	_	Charge pump capacitor pin		
C1-	4	_	Charge pump capacitor pin		
C2+	5	_	Charge pump capacitor pin		
C2-	6	_	Charge pump capacitor pin		
DIN1	13	I	Driver logic input		
DIN2	12	I	iver logic input		
DOUT1	17	0	RS-232 driver output		
DOUT2	8	0	RS-232 driver output		
ĒN	1	I	Receiver enable, active low		
GND	18	_	Ground		
NC	11,14	_	No internal connection		
PWRDOWN	20	I	Driver disable, active low		
RIN1	16	I	RS-232 receiver input		
RIN2	9	I	RS-232 receiver input		
ROUT1	15	0	Receiver logic output		
ROUT2	10	0	Receiver logic output		
V <sub>CC</sub>	19	_	Power Supply		
V+	3	_	Charge pump capacitor pin		
V-	7	_	Charge pump capacitor pin		



## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range <sup>(2)</sup>		-0.3	6	V
V+	Positive-output supply voltage range <sup>(2)</sup>	sitive-output supply voltage range <sup>(2)</sup>		7	V
V-	Negative-output supply voltage range <sup>(2)</sup>		0.3	-7	V
V+ – V–	Supply voltage difference <sup>(2)</sup>	pply voltage difference <sup>(2)</sup>		13	V
V	/ <sub>I</sub> Input voltage range	Driver ( EN, PWRDOWN)	-0.3	6	V
<b>v</b> i		Receiver	-25	25	
V		Driver	-13.2	13.2	V
Vo	Output voltage range	Receiver	-0.3	V <sub>CC</sub> + 0.3	v
TJ	Operating virtual junction temperature			150	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 All under maximum conditions are stressed to the device of the device at the second stress of the device of t

(2) All voltages are with respect to network GND.

## 6.2 ESD Ratings

				VALUE	UNIT
		Human-body model (HBM), per ANSI/	All pins except RIN1, RIN2, DOUT1 and DOUT2 pins	±3000	
V (ESD)	Electrostatic discharge	ESDA/JEDEC JS-001 <sup>(1)</sup>	RIN1, RIN2, DIN1 and DOUT2 pins to GND	±15,000	V
		Charged device model (CDM), per ANSI/ ESDA/JEDEC JS-002 <sup>(2)</sup>		±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 ESD Ratings - IEC Specifications

					VALUE	UNIT
		Electrostatic	IEC 61000-4-2 Contact Discharge (1)	Pins RIN1, RIN2, DOUT1, DOUT2 only	±8,000	V
V	(ESD)	discharge	IEC 61000-4-2 Air Discharge (1)		±15,000	v

(1) For PW package only, a minimum of 1-µF capacitor is required between V<sub>CC</sub> and GND to meet the specified IEC 61000-4-2 rating.



### 6.4 Recommended Operating Conditions

See Figure 9-1 and <sup>(1)</sup>

				MIN	NOM	MAX	UNIT
	Supply voltage		V <sub>CC</sub> = 3.3 V	3	3.3	3.6	V
	Supply voltage		V <sub>CC</sub> = 5 V	4.5	5	5.5	v
V	Driver and control high-level input voltage	DIN, EN, PWRDOWN	V <sub>CC</sub> = 3.3 V	2			v
VIH	Driver and control high-level input voltage		V <sub>CC</sub> = 5 V	2.4			v
VIL	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	V
VI	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
VI	Receiver input voltage			-25		25	V
т	Operating free-air temperature		TRSF3222EC	0		70	°C
T <sub>A</sub>			TRSF3222EI	-40		85	

(1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

### 6.5 Thermal Information

			TRSF3222E		
	THERMAL METRIC <sup>(1)</sup>	DB (SSOP)	DW (SOIC)	PW (TSSOP)	UNIT
		20 Pins	20 Pins	20 Pins	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	70	58	94.1	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	33.6	30.0	35.2	°C/W
TLΨ	Junction-to-top characterization parameter	36.4	29.6	45.5	°C/W
Ψ ЈВ	Junction-to-board characterization parameter	4.8	7.7	3.1	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	35.9	29.3	45.1	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

## **6.6 Electrical Characteristics**

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

	PARAMETER	TEST CONDITIONS <sup>(2)</sup>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
I <sub>I</sub>	Input leakage current ( EN, PWRDOWN)			±0.01	±1	μA
1	Supply current	No load, PWRDOWN at V <sub>CC</sub>		0.3	1	mA
ICC	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μΑ

(1) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

(2) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

## 6.7 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

	PARAMETER	TEST CONDI	MIN	TYP <sup>(1)</sup>	MAX	UNIT	
V <sub>OH</sub>	High-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	DIN = GND	5	5.4		V
V <sub>OL</sub>	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V <sub>CC</sub>	-5	-5.4		V
I <sub>IH</sub>	High-level input current	V <sub>I</sub> = V <sub>CC</sub>			±0.01	±1	μA
IIL	Low-level input current	V <sub>I</sub> at GND		±0.01	±1	μA	
I <sub>OS</sub> Short-circuit output current <sup>(2)</sup>	V <sub>CC</sub> = 3.6 V	$V_{0} = 0 V$		±35	±60	mA	
I <sub>OS</sub>	Chon-circuit output current	V <sub>CC</sub> = 5.5 V	v0 - o v		100	±00	ША
r <sub>o</sub>	Output resistance	$V_{CC}$ , V+, and V– = 0 V,	$V_0 = \pm 2 V$	300	10M		Ω
	Output leakage current	PWRDOWN = GND	$V_{CC} = 3 V \text{ to } 3.6 V,$ $V_{O} = \pm 12 V$			±25	
l <sub>oz</sub>		FWRDOWN - GND	$V_{CC}$ = 4.5 V to 5.5 V, V <sub>O</sub> = ±10 V			±25	μA

(1)

All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one (2) output should be shorted at a time.

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. (3)

### 6.8 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

	PARAMETER		TEST CONDITIONS <sup>(3)</sup>		MIN	TYP <sup>(1)</sup>	MAX	UNIT
			C <sub>L</sub> = 1000 pF		250			
	Maximum data rate (See Figure 7-1)	$R_L = 3 k\Omega$ , One DOUT switching	C <sub>L</sub> = 250 pF,	$V_{CC}$ = 3 V to 4.5 V	1000			kbit/s
		sine 2001 childrening	$C_L$ = 1000 pF, $V_{CC}$ = 4.5 V to 5.5 V		1000			
t <sub>sk(p)</sub>	Pulse skew <sup>(2)</sup>	C <sub>L</sub> = 150 pF to 2500 pF,	$R_L = 3 k\Omega$ to 7 k $\Omega$ ,	See Figure 7-2		300		ns
	Slew rate.	$R_L = 7 k\Omega$ ,	C <sub>L</sub> = 150 pF to 1000 pF		8		90	
	transition region	R <sub>I</sub> = 3 kΩ	C <sub>L</sub> = 1000 pF		12		60	V/µs
	(see Figure 7-1)		C <sub>L</sub> = 150 pF to 250 pF		24		150	

(1) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

(2)

Pulse skew is defined as  $|t_{PLH} - t_{PHL}|$  of each channel of the same device. Test conditions are C1–C4 = 0.1 µF at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V<sub>CC</sub> = 5 V ± 0.5 V. (3)



### 6.9 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

	PARAMETER	TEST CONDITIONS <sup>(2)</sup>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> - 0.6	V <sub>CC</sub> - 0.1		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
		V <sub>CC</sub> = 3.3 V		1.5	2.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.8	2.4	v
v	Negative-going input threshold voltage	V <sub>CC</sub> = 3.3 V	0.6	1.2		V
V <sub>IT-</sub>	Negative-going input the should voltage	V <sub>CC</sub> = 5 V	0.8	1.5		v
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> – V <sub>IT–</sub> )			0.3		V
I <sub>oz</sub>	Output leakage current	ĒN = 1		±0.05	±10	μA
r <sub>i</sub>	Input resistance	$V_1 = \pm 3 V$ to $\pm 25 V$	3	5	7	kΩ

All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. (1)

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. (2)

### 6.10 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS <sup>(3)</sup>	TYP <sup>(1)</sup>	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	C <sub>L</sub> = 150 pF, See Figure 7-3	300	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF, See Figure 7-3	300	ns
t <sub>en</sub>	Output enable time	$C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 7-4	200	ns
t <sub>dis</sub>	Output disable time	$C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 7-4	200	ns
t <sub>sk(p)</sub>	Pulse skew <sup>(2)</sup>	See Figure 7-3	300	ns

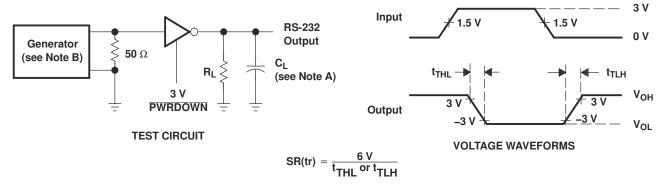
All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. (1)

(2)

Pulse skew is defined as  $|t_{PLH} - t_{PHL}|$  of each channel of the same device. Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. (3)



## **7 Parameter Measurement Information**



A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns.  $t_f \le 10$  ns.

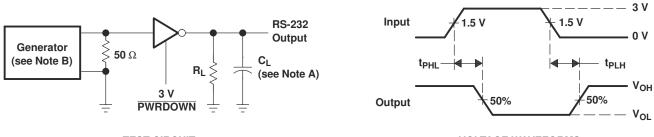


Figure 7-1. Driver Slew Rate

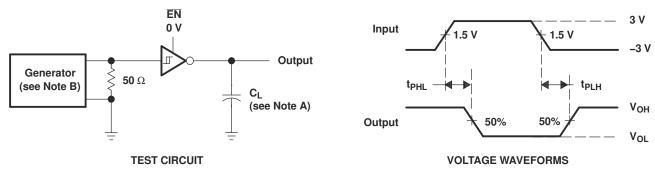
TEST CIRCUIT

VOLTAGE WAVEFORMS

A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 7-2. Driver Pulse Skew

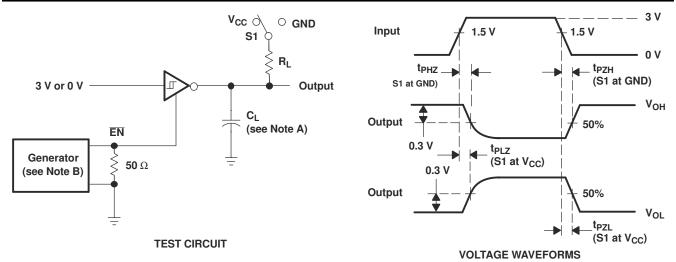


A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 7-3. Receiver Propagation Delay Times





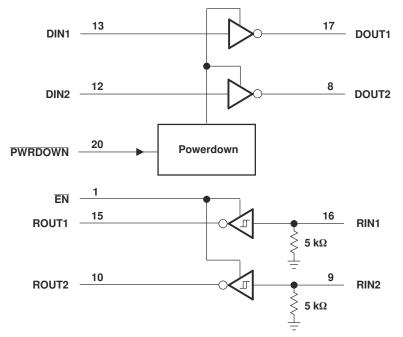
- A. C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics:  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.





## 8 Detailed Description

## 8.1 Functional Block Diagram



A. Pin numbers shown are for the DB, DW, and PW packages.

## Figure 8-1. Logic Diagram (Positive Logic)

### 8.2 Device Functional Modes

la	Die 8-1. Function	Table: Each Driver
	INPUTS <sup>(1)</sup>	OUTPUT
DIN	PWRDOWN	DOUT

~

atian Tables Faab Driver

DIN	PWRDOWN	DOUT
Х	L	Z
L	Н	н
Н	Н	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

INPUTS <sup>(1)</sup>		OUTPUT				
RIN	EN	ROUT				
L	L	Н				
н	L	L				
х	Н	Z				
Open	L	н				

(1) H = high level, L = low level, X = irrelevant,
 Z = high impedance (off),

Open = input disconnected or connected driver off



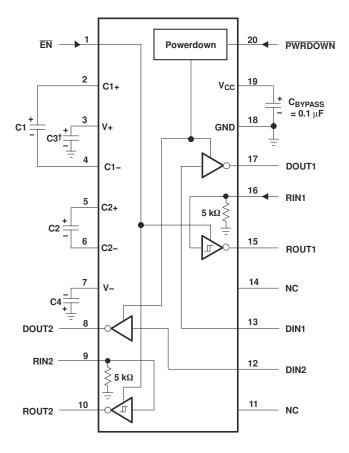
# 9 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

### 9.2 Typical Application



 $^{\dagger}$  C3 can be connected to  $V_{CC}$  or GND.

- NOTES: A. Resistor values shown are nominal.
  - B. NC No internal connection
  - C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V <sub>CC</sub> vs CAPACITOR VALUES											
v <sub>cc</sub>	C1	C2, C3, and C4									
3.3 V $\pm$ 0.3 V	<b>0.1</b> μ <b>F</b>	<b>0.1</b> μF									
5 V $\pm$ 0.5 V	<b>0.047</b> μ <b>F</b>	<b>0.33</b> μF									
3 V to 5.5 V	<b>0.1</b> μF	<b>0.47</b> μ <b>F</b>									

V VI CARACITOR VALUES

### Figure 9-1. Typical Operating Circuit and Capacitor Values



## 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### **10.1 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### **10.2 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

### 10.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

### **10.4 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	. ,					.,	(6)				
TRSF3222ECDB	ACTIVE	SSOP	DB	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	RT22EC	Samples
TRSF3222EIDWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRSF3222EI	Samples
TRSF3222EIPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT22EI	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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Texas

STRUMENTS

## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRSF3222EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
TRSF3222EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
TRSF3222EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1



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# PACKAGE MATERIALS INFORMATION

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRSF3222EIDWR	SOIC	DW	20	2000	367.0	367.0	45.0
TRSF3222EIPWR	TSSOP	PW	20	2000	356.0	356.0	35.0
TRSF3222EIPWR	TSSOP	PW	20	2000	356.0	356.0	35.0

## TEXAS INSTRUMENTS

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## TUBE



## - B - Alignment groove width

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TRSF3222ECDB	DB	SSOP	20	70	530	10.5	4000	4.1

# **DB0020A**



# **PACKAGE OUTLINE**

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



# DB0020A

# **EXAMPLE BOARD LAYOUT**

# SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DB0020A

# **EXAMPLE STENCIL DESIGN**

# SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **DW0020A**



# **PACKAGE OUTLINE**

## SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



# DW0020A

# **EXAMPLE BOARD LAYOUT**

# SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DW0020A

# **EXAMPLE STENCIL DESIGN**

# SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **PW0020A**



# **PACKAGE OUTLINE**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0020A

# **EXAMPLE BOARD LAYOUT**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0020A

# **EXAMPLE STENCIL DESIGN**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# LAND PATTERN DATA



NOTES: Α. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
  C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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